

MM54HC240/MM74HC240/MM54HC241/MM74HC241



T-52-09

MM54HC240/MM74HC240
Inverting Octal TRI-STATE® Buffer
MM54HC241/MM74HC241 Octal TRI-STATE Buffer

General Description

These TRI-STATE buffers utilize advanced silicon-gate CMOS technology. They possess high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits achieve speeds comparable to low power Schottky devices, while retaining the advantage of CMOS circuitry, i.e., high noise immunity and low power consumption. Each has a fanout of 15 LS-TTL equivalent inputs.

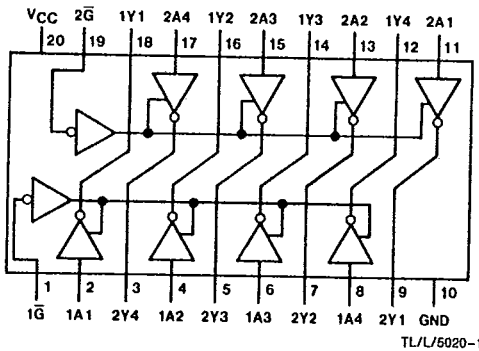
The MM54HC240/MM74HC240 is an inverting buffer and has two active low enables (1G and 2G). Each enable independently controls 4 buffers. MM54HC241/MM74HC241 is a non-inverting buffer that has one active low enable and one active high enable, each again controlling 4 buffers. Neither device has Schmitt trigger inputs.

All inputs are protected from damage due to static discharge by diodes to VCC and ground.

Features

- Typical propagation delay: 12 ns
- TRI-STATE outputs for connection to system buses
- Wide power supply range: 2-6V
- Low quiescent supply current: 80 µA (74 Series)
- Output current: 6 mA

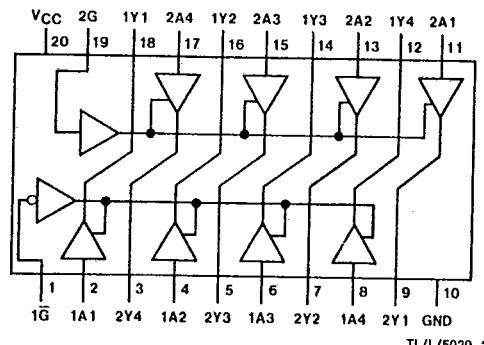
Connection Diagrams Dual-In-Line Packages



Top View

Order Number MM54HC240/241* or MM74HC240/241*

*Please look into Section 8, Appendix D for availability of various package types.



Top View

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Truth Tables

(HC240)

1G	1A	1Y	2G	2A	2Y
L	L	H	L	L	H
L	H	L	L	H	L
H	L	Z	H	L	Z
H	H	Z	H	H	Z

H = high level, L = low level, Z = high impedance

(HC241)

1G	1A	1Y	2G	2A	2Y
L	L	L	L	L	Z
L	H	H	L	H	Z
H	L	Z	H	L	L
H	H	Z	H	H	H



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Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.5 to +7.0V
DC Input Voltage (V _{IN})	-1.5 to V _{CC} +1.5V
DC Output Voltage (V _{OUT})	-0.5 to V _{CC} +0.5V
Clamp Diode Current (I _{IK} , I _{OK})	±20 mA
DC Output Current, per pin (I _{OUT})	±35 mA
DC V _{CC} or GND Current, per pin (I _{CC})	±70 mA
Storage Temperature Range (T _{STG})	-65°C to +150°C
Power Dissipation (P _D)	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T _L) (Soldering 10 seconds)	260°C

Operating Conditions T-52-09

Supply Voltage (V _{CC})	Min 2	Max 6	Units V
DC Input or Output Voltage (V _{IN} , V _{OUT})	0	V _{CC}	V
Operating Temp. Range (T _A)			
MM74HC	-40	+85	°C
MM54HC	-55	+125	°C
Input Rise or Fall Times (t _r , t _f)			
V _{CC} =2.0V		1000	ns
V _{CC} =4.5V		500	ns
V _{CC} =6.0V		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V _{CC}	T _A = 25°C			Units	
				74HC T _A = -40 to 85°C				54HC T _A = -55 to 125°C
				Typ	Guaranteed Limits			
V _{IH}	Minimum High Level Input Voltage		2.0V	1.5	1.5	1.5	V	
			4.5V	3.15	3.15	3.15	V	
			6.0V	4.2	4.2	4.2	V	
V _{IL}	Maximum Low Level Input Voltage**		2.0V	0.5	0.5	0.5	V	
			4.5V	1.35	1.35	1.35	V	
			6.0V	1.8	1.8	1.8	V	
V _{OH}	Minimum High Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 20 μA	2.0V	2.0	1.9	1.9	V	
			4.5V	4.5	4.4	4.4	V	
			6.0V	6.0	5.9	5.9	V	
		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 6.0 mA I _{OUT} ≤ 7.8 mA	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
V _{OL}	Maximum Low Level Output Voltage	V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 20 μA	2.0V	0	0.1	0.1	V	
			4.5V	0	0.1	0.1	V	
			6.0V	0	0.1	0.1	V	
		V _{IN} = V _{IH} or V _{IL} I _{OUT} ≤ 6.0 mA I _{OUT} ≤ 7.8 mA	4.5V	0.2	0.26	0.33	0.4	V
			6.0V	0.2	0.26	0.33	0.4	V
I _{IN}	Maximum Input Current	V _{IN} = V _{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I _{OZ}	Maximum TRI-STATE Output Leakage Current	V _{IN} = V _{IH} or V _{IL} V _{OUT} = V _{CC} or GND G̅ = V _{IH} , G = V _{IL}	6.0V		±0.5	±5	±10	μA
I _{CC}	Maximum Quiescent Supply Current	V _{IN} = V _{CC} or GND I _{OUT} = 0 μA	6.0V		8.0	80	160	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.
Note 2: unless otherwise specified all voltages are referenced to ground.
Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.
Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH} and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.
 **V_{IL} limits are currently tested at 20% of V_{CC}. The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

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AC Electrical Characteristics MM54HC240/MM74HC240 $V_{CC}=5V, T_A=25^\circ C, t_r=t_f=6 ns$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay	$C_L = 45 pF$	12	18	ns
t_{PZH}, t_{PZL}	Maximum Enable Delay to Active Output	$R_L = 1 k\Omega$ $C_L = 45 pF$	14	28	ns
t_{PHZ}, t_{PLZ}	Maximum Disable Delay from Active Output	$R_L = 1 k\Omega$ $C_L = 5 pF$	13	25	ns

AC Electrical Characteristics MM54HC240/MM74HC240

$V_{CC}=2.0V to 6.0V, C_L=50 pF, t_r=t_f=6 ns$ (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	$T_A = 25^\circ C$		74HC	54HC	Units
						$T_A = -40 to 85^\circ C$	$T_A = -55 to 125^\circ C$	
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay	$C_L = 50 pF$	2.0V	55	100	126	149	ns
			2.0V	80	150	190	224	ns
		$C_L = 150 pF$	4.5V	12	20	25	30	ns
			4.5V	22	30	38	45	ns
		6.0V	11	17	21	25	ns	
6.0V	28	26	32	38	ns			
t_{PZH}, t_{PZL}	Maximum Output Enable Time	$R_L = 1 k\Omega$ $C_L = 50 pF$	2.0V	75	150	189	224	ns
			2.0V	100	200	252	298	ns
		$C_L = 150 pF$	4.5V	15	30	38	45	ns
			4.5V	20	40	50	60	ns
		6.0V	13	26	32	38	ns	
6.0V	17	34	43	51	ns			
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time	$R_L = 1 k\Omega$ $C_L = 50 pF$	2.0V	75	150	189	224	ns
			4.5V	15	30	38	45	ns
			6.0V	13	26	32	38	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V		60	75	90	ns
			4.5V		12	15	18	ns
			6.0V		10	13	15	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per buffer) $\bar{G} = V_{IH}$ $\bar{G} = V_{IL}$		12				pF
				50				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF
C_{OUT}	Maximum Output Capacitance			10	20	20	20	pF

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MM54HC241/MM74HC241/MM54HC240/MM74HC240

AC Electrical Characteristics MM54HC241/MM74HC241 $V_{CC}=5V, T_A=25^\circ C, t_r=t_f=6 ns$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units	
t_{PHL}, t_{PLH}	Maximum Propagation Delay	$C_L=45 pF$	13	20	ns	
t_{PZH}, t_{PZL}	Maximum Enable Delay to Active Output	$R_L=1 k\Omega$	$1\bar{G}$	17	28	ns
		$C_L=45 pF$	$2\bar{G}$	17	28	ns
t_{PHZ}, t_{PLZ}	Maximum Disable Delay from Active Input	$R_L=1 k\Omega$	$1\bar{G}$	15	25	ns
		$C_L=5 pF$	$2\bar{G}$	13	25	ns

AC Electrical Characteristics MM54HC241/MM74HC241

$V_{CC}=2.0V$ to $6.0V, C_L=50 pF, t_r=t_f=6 ns$ (unless otherwise specified)

Symbol	Parameter	Conditions	V_{CC}	$T_A=25^\circ C$		74HC	54HC	Units
						$T_A=-40$ to $85^\circ C$	$T_A=-55$ to $125^\circ C$	
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay	$C_L=50 pF$	2.0V	58	115	145	171	ns
			2.0V	83	165	208	246	ns
		$C_L=150 pF$	4.5V	14	23	29	34	ns
			4.5V	17	33	42	49	ns
		$C_L=50 pF$	6.0V	10	20	25	29	ns
			6.0V	14	28	35	42	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time	$R_L=1 k\Omega$	2.0V	75	150	189	224	ns
			2.0V	100	200	252	298	ns
		$C_L=50 pF$	4.5V	15	30	38	45	ns
			4.5V	20	40	50	60	ns
		$C_L=50 pF$	6.0V	13	26	32	38	ns
			6.0V	17	34	43	51	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time	$R_L=1 k\Omega$	2.0V	75	150	189	224	ns
			4.5V	15	30	38	45	ns
			6.0V	13	26	32	38	ns
t_{TLH}, t_{THL}	Maximum Output Rise and Fall Time		2.0V		60	75	90	ns
			4.5V		12	15	18	ns
			6.0V		10	13	15	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per buffer) $G=V_{IL}, \bar{G}=V_{IH}$ $G=V_{IH}, \bar{G}=V_{IL}$		12 50				pF pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF
C_{OUT}	Maximum Output Capacitance			10	20	20	20	pF

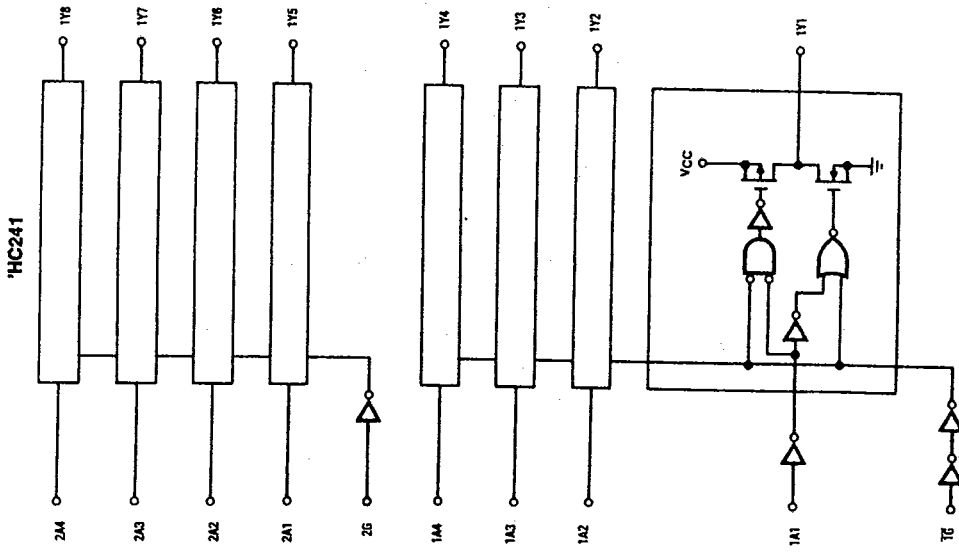
Note 5: C_{PD} determines the no load dynamic power consumption, $P_D=C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S=C_{PD} V_{CC} f + I_{CC}$.

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Logic Diagrams

MM54HC240/MM74HC240/MM54HC241/MM74HC241

3-0205/7/L



TL/J/5020-4

